

# Characterization of Silicon n-in-p Pixel Sensors for future ATLAS Upgrades



Christian Gallrapp<sup>1</sup>

A. La Rosa<sup>2</sup>, A. Macchiolo<sup>3</sup>, R. Nisius<sup>3</sup>,  
H. Pernegger<sup>1</sup>, R. H. Richter<sup>4</sup>, P. Weigell<sup>3</sup>

<sup>1</sup>CERN

<sup>2</sup>Université de Genève

<sup>3</sup>Max-Planck-Institut für Physik

<sup>4</sup>MPI-Halbleiterlabor

# ATLAS Pixel Detector upgrade

2013

- ATLAS Insertable B-Layer (IBL)
  - Planar n-in-n, 3D n-in-p sensors

2018

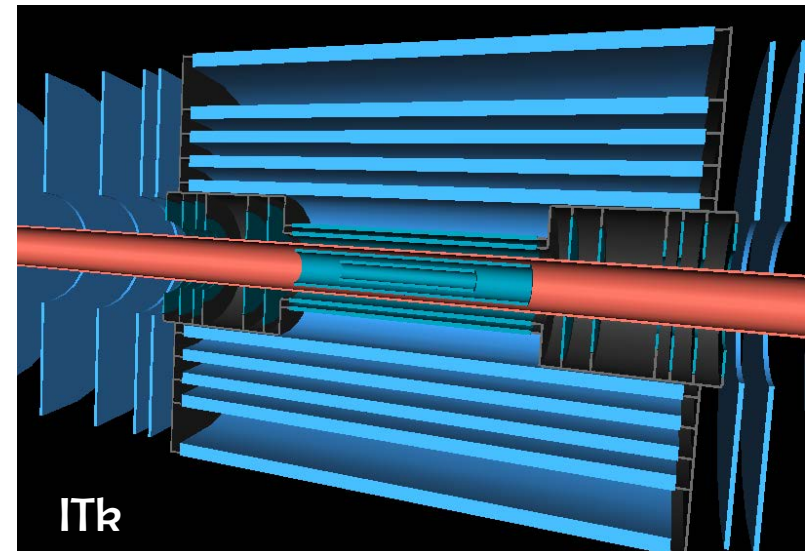
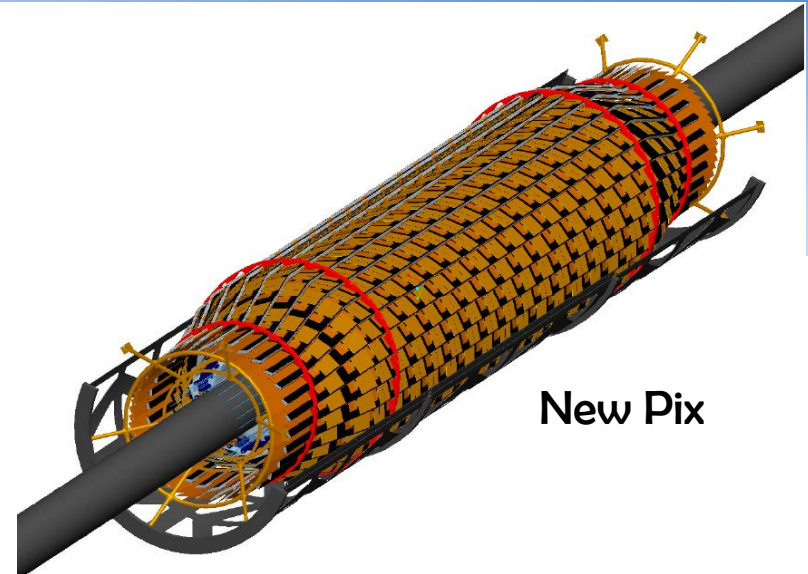
- Phase 1 upgrade: New Pix
  - Full replacement depending on performance (Under discussion)
  - Luminosity:  $(2-3) \cdot 10^{34} \text{ cm}^{-2}\text{s}^{-1}$
  - Radiation dose:  $5 \cdot 10^{15} \text{ n}_{\text{eq}}\text{cm}^{-2}$  or higher

2022

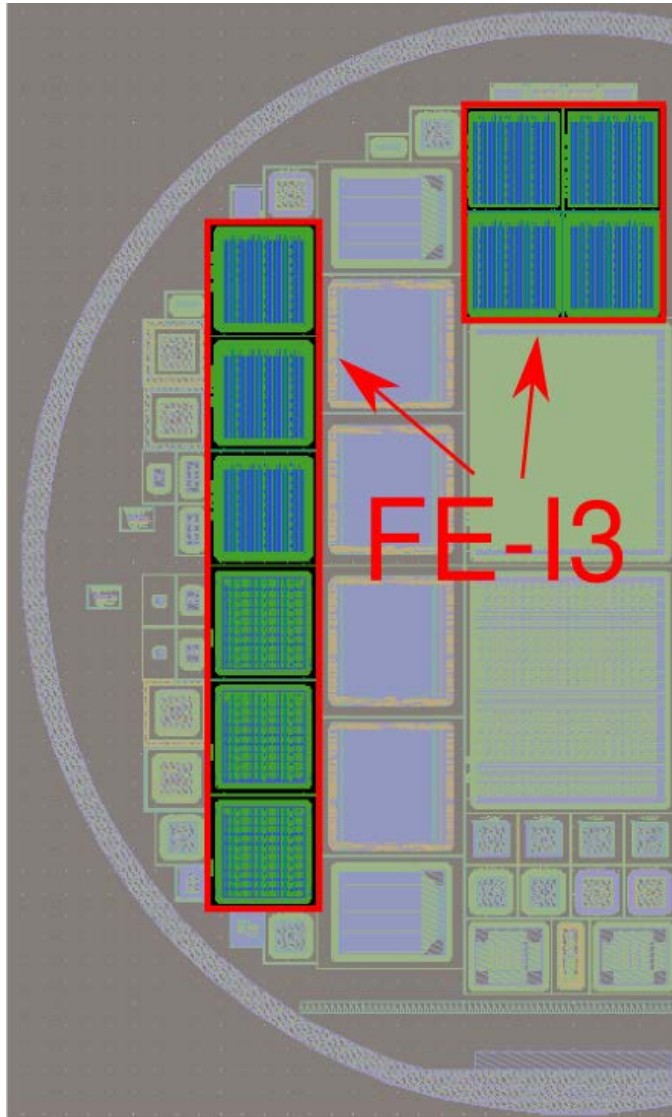
- Phase 2 upgrade: Inner detector Tracker (ITk)
  - Complete new ATLAS tracker for pixels and strip detectors
  - Luminosity:  $5 \cdot 10^{34} \text{ cm}^{-2}\text{s}^{-1}$
  - Radiation dose:  $2 \cdot 10^{16} \text{ n}_{\text{eq}}\text{cm}^{-2}$

Planar n-in-p as future sensor technologie

- Excellent candidate for large volumes
- Single-sided processing -> reduced cost.
- Radiation hardness comparable to n-in-n
- R&D based on present ATLAS front-end chip



# CiS-Production



18 Fz n-in-p wafer, 285 $\mu$ m thick delivered by CiS (Erfurt, Germany)

10 FE-I3: Single Chip Modules (SCM) with different guard ring (GR) and isolation schemes:

- 2·8 GRs, homogeneous p-spray
- 2·15 GRs, homogeneous p-spray
- 3·Standard (19) GR, homogeneous p-spray
- 3·Standard (19) GR, moderated p-spray

19 SCMs were built by IZM.

Assembling and wire-bonding done in Bonn.

# Benzo Cyclo Butene

## Planar n-in-p sensors

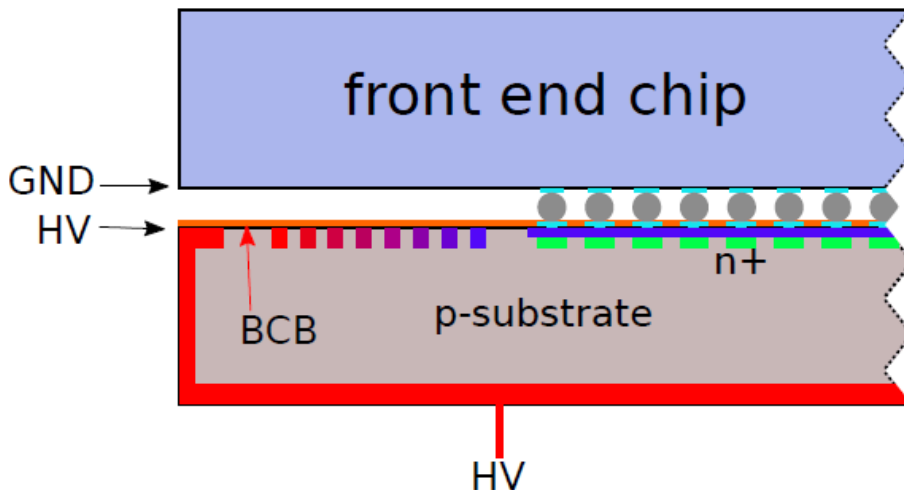
- High voltage on the sensor reaches the side facing the front-end chip
- This might cause sparks which would destroy the chip

## Possible Solution

- Thin layer of Benzo Cyclo Butene (BCB) to cover the sensor
- BCB provides higher electrical insulation capability than  $\text{SiO}_2$

## Results

- HV-stability observed several hours at voltages up to 1000V



A decorative graphic consisting of several horizontal blue lines of varying lengths and thicknesses, intersected by a vertical blue line on the right side, creating a cross-like pattern.

# **CIS FE-13 RESULTS**

# Irradiation

## CERN (protons 24GeV)

- 1 sensor at  $6.2 \cdot 10^{14} n_{eq} cm^{-2}$
- 1 sensor at  $2.5 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 sensor at  $4.4 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 SCM at  $2.8 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 SCM at  $5 \cdot 10^{15} n_{eq} cm^{-2}$

## Karlsruhe (protons 25MeV)

- 1 SCM at  $10^{15} n_{eq} cm^{-2}$

## Ljubljana (neutrons)

- 1 SCM at  $2 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 SCM at  $3 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 SCM at  $5 \cdot 10^{15} n_{eq} cm^{-2}$
- 1 SCM at  $10^{16} n_{eq} cm^{-2}$

## Mixed irradiation

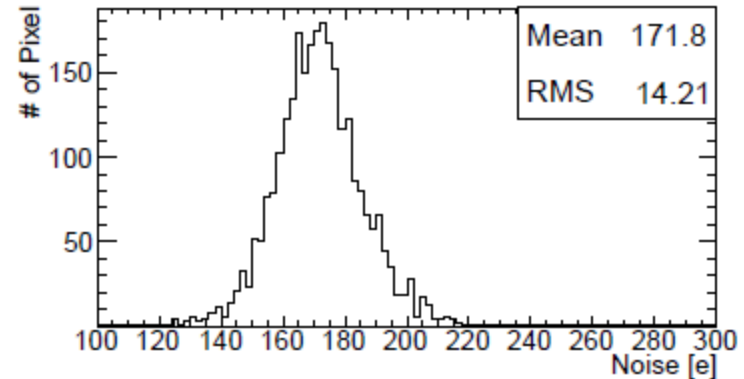
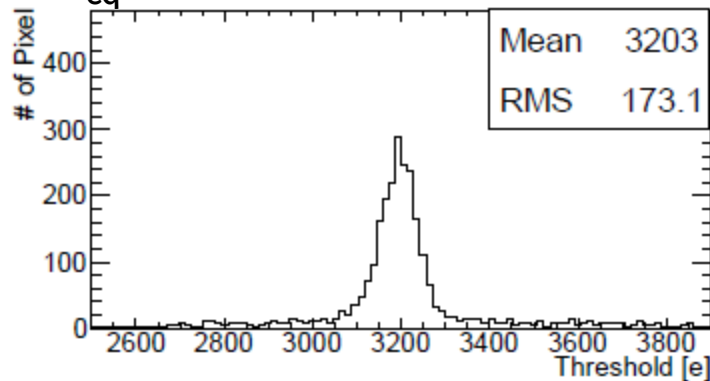
(Ljubljana+Karlsruhe)

- 1 SCM at  $10^{15} n_{eq} cm^{-2} + 10^{15} n_{eq} cm^{-2}$

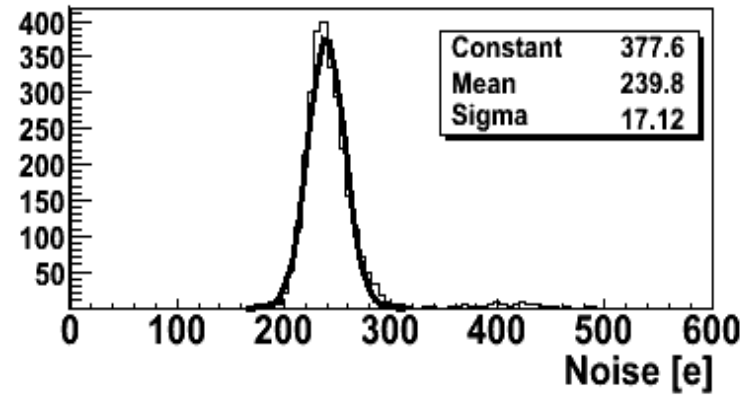
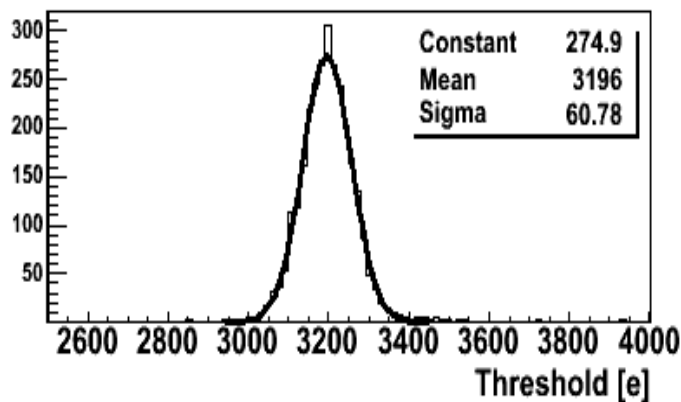
# Tuning of irradiated sample

Irradiation effects sensor and front-end properties which influence the tuning behavior

- $5 \cdot 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  neutron irradiated: tuning at 1000V and  $-60^\circ\text{C}$



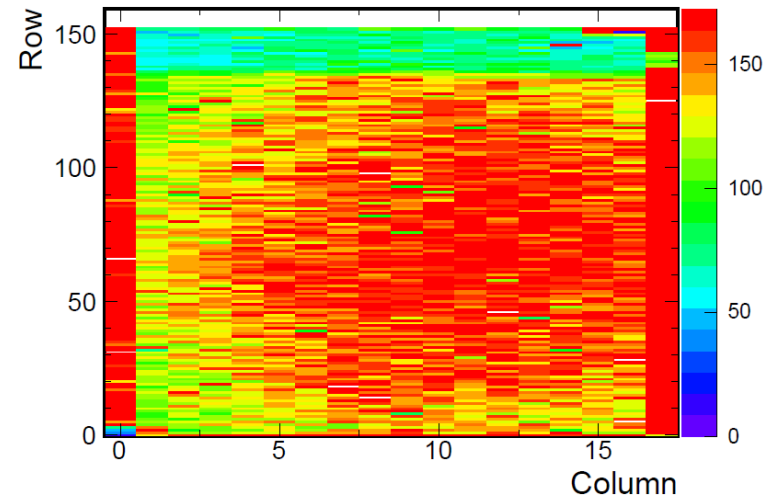
- $10^{16} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  neutron irradiated: tuning at 950V and  $-50^\circ\text{C}$



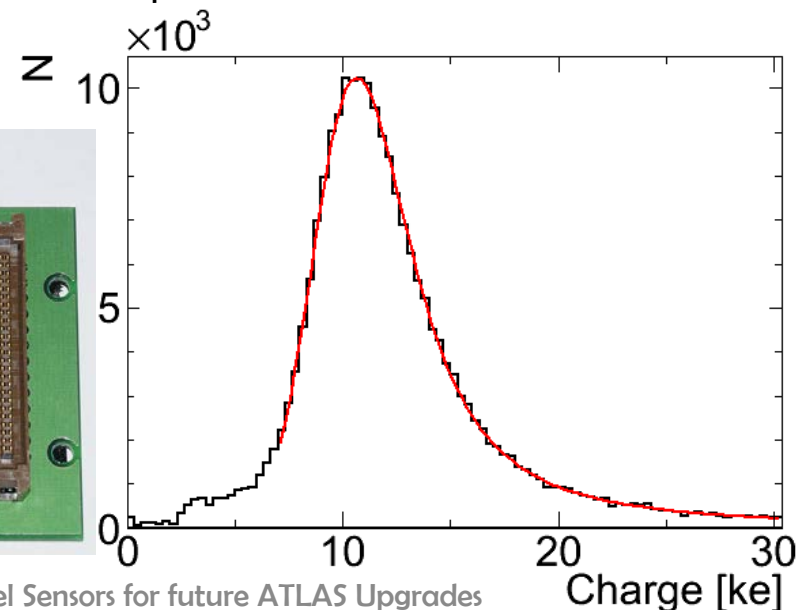
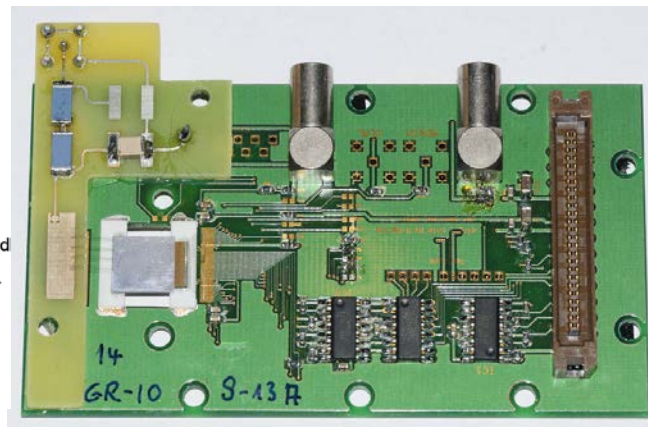
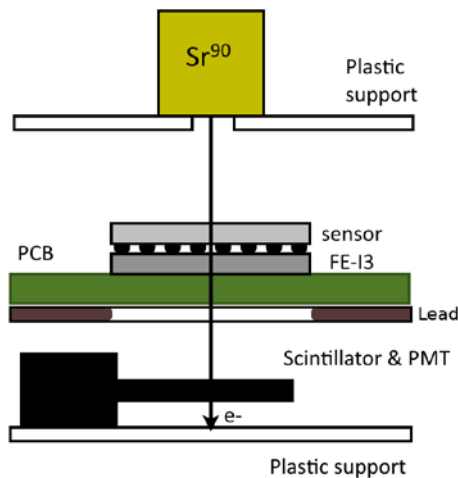
Tuning is still possible with satisfying results

# Sr-90 source tests

- Sr-90 source is used for charge collection measurement
- External trigger via scintillator
- Measurement done for fluences up to  $5 \cdot 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  and 1000V
- Events with two independent clusters are discarded in order to minimize noise



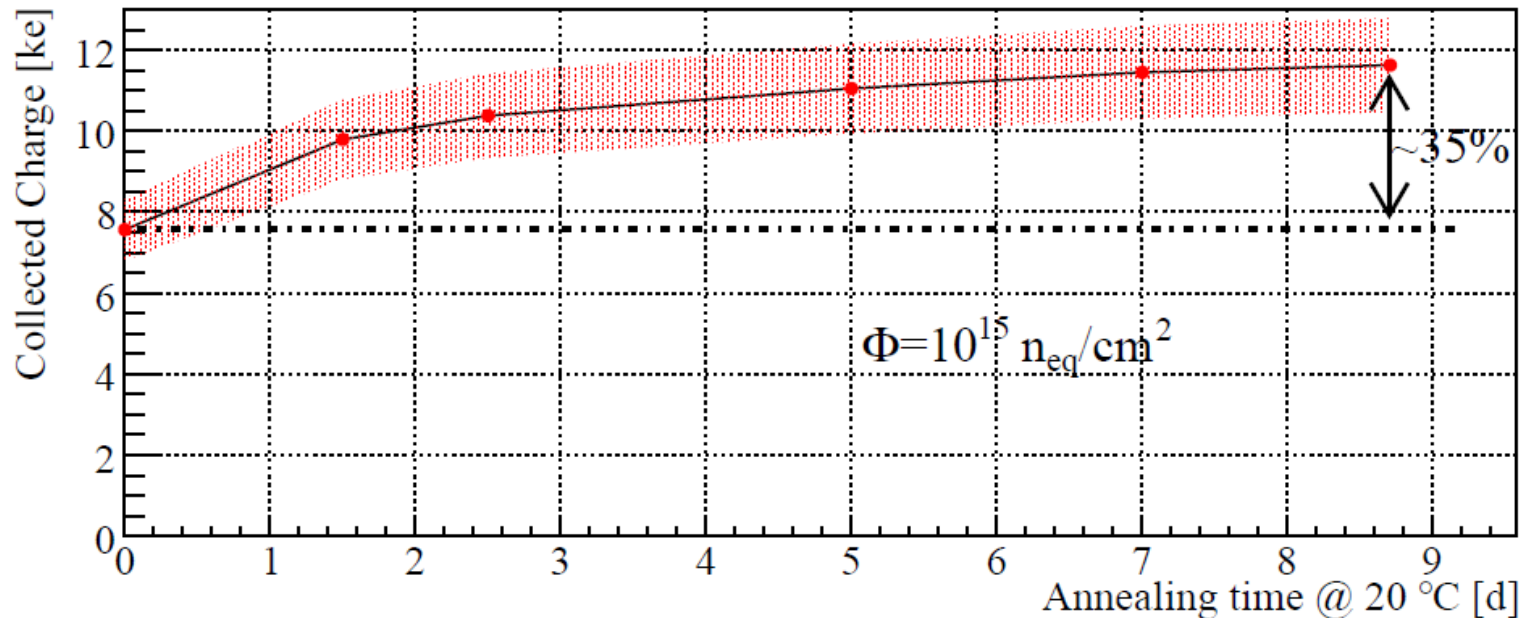
$5 \cdot 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  neutron irradiated at 1000V





# Annealing studie

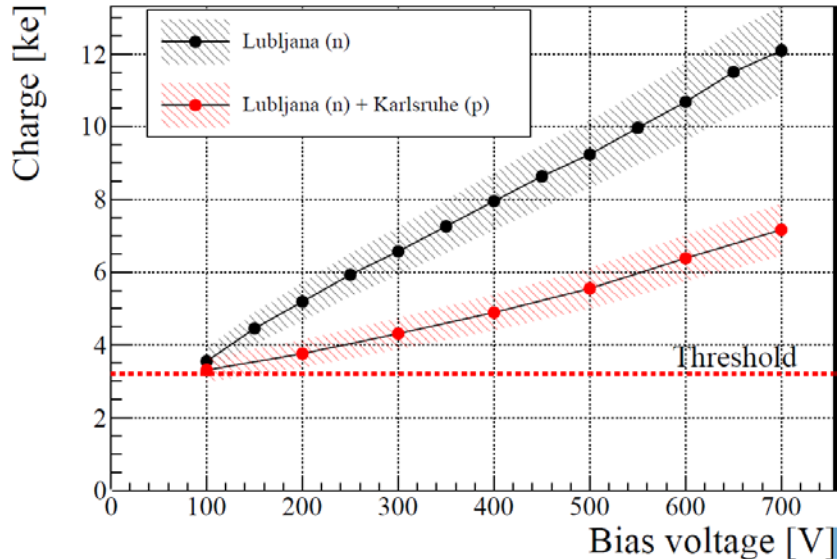
- Proton irradiation at KIT possible with SCM on PCB
- Neutron irradiation needs handling (gluing, bonding) after irradiation (annealing 1-2 days)



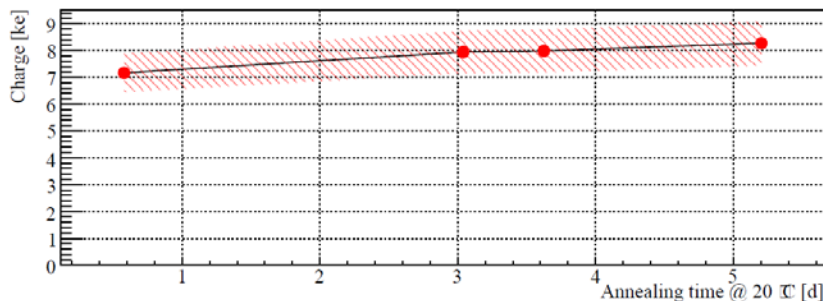
- Uncertainties arise from limited knowledge of capacitors used in ToT to charge transformation

# Mixed irradiation

One SCM was twice irradiated :  $10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  (LJ) +  $10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$  (KIT)

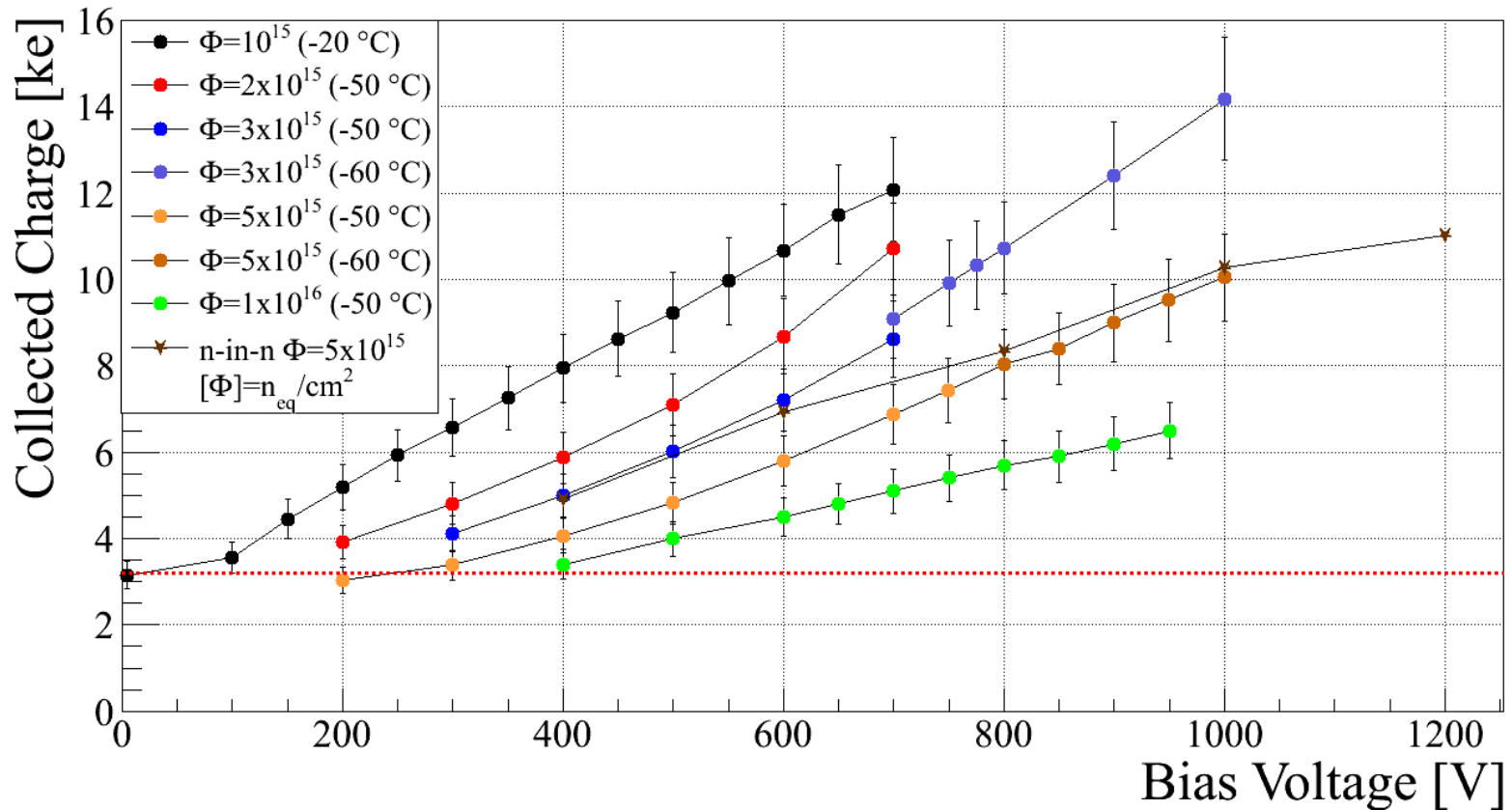


- Sufficient charge collection after irradiation
- Measurements at higher voltages limited by HV capabilities of PCB
- Compared to unirradiated sensors the collected charge at 700V is
  - 65% after irradiation in Ljubljana
  - 39% after both irradiations
- Low noise between  $100e^-$  and  $120e^-$



Measurements done at  $-20^\circ\text{C}$  (Ljubljana) and  $-50^\circ\text{C}$  (Ljubljana + Karlsruhe)

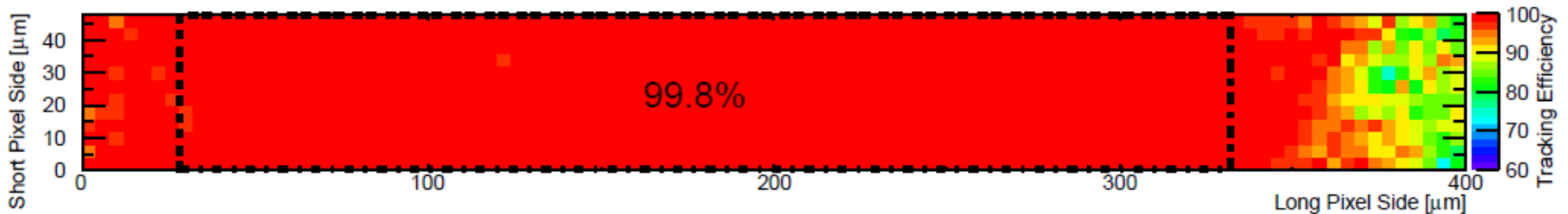
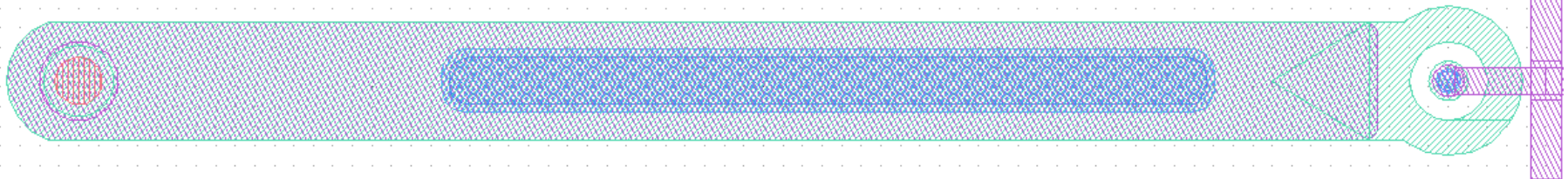
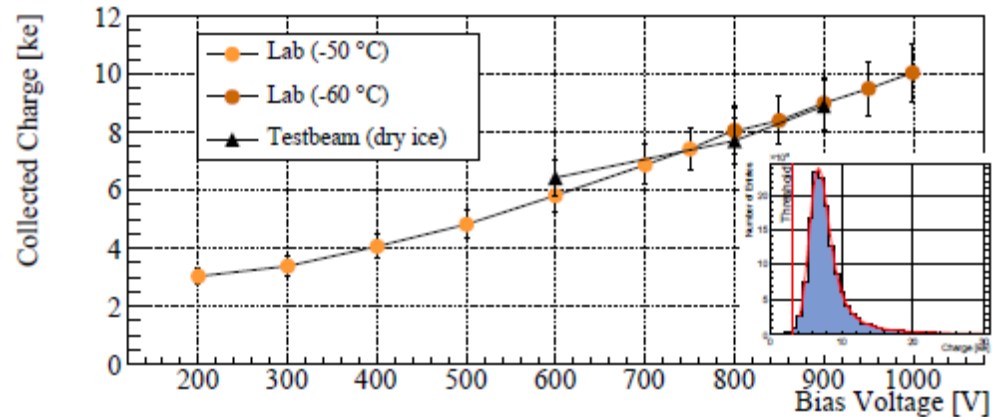
# Charge collection



- All neutron samples were annealed for around two days
- Highest leakage currents  $\sim 20 \mu\text{A}$
- n-in-n sample data from S. Altenheiner et al. (doi:10.1016/j.nima.2011.05.074)

# Testbeam results at $5 \cdot 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$

- TB with 120GeV  $\pi$ -beam at CERN SPS + Eudet telescope
- Neutron Irradiated Sample ( $5 \cdot 10^{15} \text{ n}_{\text{eq}} \text{ cm}^{-2}$ )
- Threshold of  $3.2 \text{ ke}^-$  (MPV  $6.4 \text{ ke}^-$ )
- Efficiency at 600V: 98.7% overall
- (99,8% in central region)

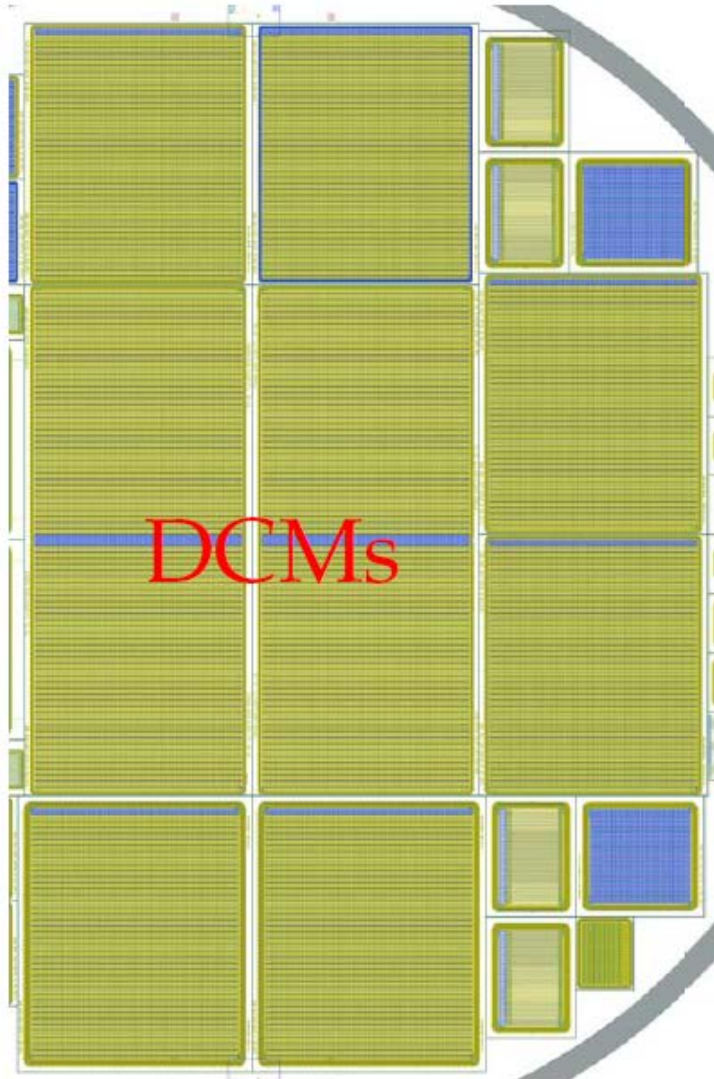


**TB-Group 2011:** S. Altenheiner, M. Backhaus, M. Bomben, D. Forshaw, Ch. Gallrapp, M. George, J. Idarraga, J. Janssen, J. Jentsch, T. Lapsien, A. La Rosa, A. Macchiolo, G. Marchiori, R. Nagai, C. Nellist, I. Rubinskiy, A. Rummler, G. Troska, Y. Unno, P. Weigell, J. Weingarten

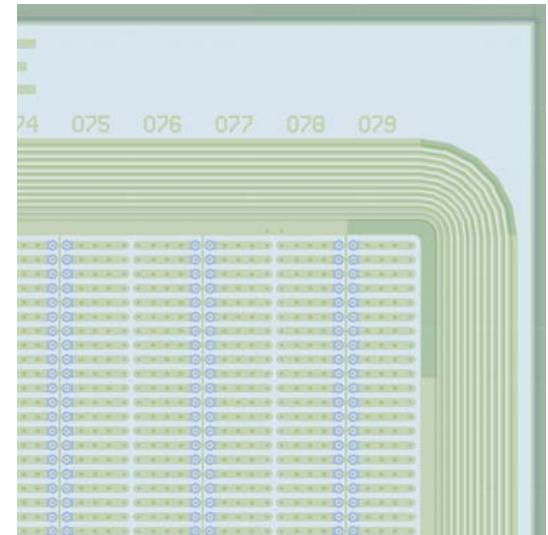
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# **NEW CIS FE-14 PRODUCTION**

# New CiS FE-I4 Production



- Pixel sensors compatible with FE-I4 (new ATLAS read-out chip)
- 6 Single Chip Module
- 2 Double Chip Module
- Thinner bulk: 150 $\mu\text{m}$  and 200 $\mu\text{m}$ 
  - Higher CCE after irradiations.
  - Less material in crucial part of the detector
- Guard-rings are following the IBL design:
  - 450 $\mu\text{m}$  inactive edge
- Pitch: 50 $\cdot$ 250 $\mu\text{m}^2$



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# **SUMMARY AND OUTLOOK**



# Summary and outlook

## Summary

- SCM properly working up to  $10^{16} n_{\text{eq}}\text{cm}^{-2}$
- Stable operation at 1000V for several hours.
- Charge collection for voltages higher than 600V well above threshold ( $3.2\text{ke}^-$ ) up to  $10^{16} n_{\text{eq}}\text{cm}^{-2}$
- High efficiency >98% at  $5 \cdot 10^{15} n_{\text{eq}}\text{cm}^{-2}$  already at 600V

## Outlook

- Test beam measurements with  $10^{16} n_{\text{eq}}\text{cm}^{-2}$  neutron irradiated samples will follow
- Testbeam analysis including tracking efficiency for  $10^{16} n_{\text{eq}}\text{cm}^{-2}$
- Compare results with the new FE-I4 based production which hopefully arrives soon.



# Acknowledgements



- A. Dierlamm(KIT) for performing the proton irradiation in Karlsruhe
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**THANK YOU FOR YOUR  
ATTENTION**